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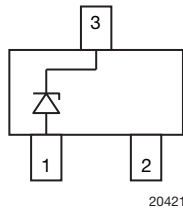
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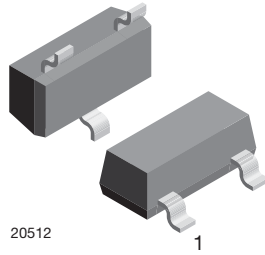
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Single-Line ESD Protection in SOT-23



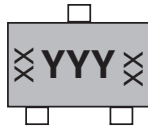
20421



20512

1

MARKING (example only)



20357

YYY = type code (see table below)

XX = date code

FEATURES

- Single-line ESD-protection device
- ESD-protection acc. IEC 61000-4-2
± 30 kV contact discharge
± 30 kV air discharge
- ESD capability according to AEC-Q101:
human body model: class H3B: > 8 kV
- Space saving SOT-23 package
- e3 - Sn
- AEC-Q101 qualified available
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION							
PART NUMBER (EXAMPLE)	ENVIRONMENTAL AND QUALITY CODE				PACKAGING CODE		ORDERING CODE (EXAMPLE)
	AEC-Q101 QUALIFIED	RoHS-COMPLIANT + LEAD (Pb)-FREE		TIN PLATED	3K PER 7" REEL (8 mm TAPE), 15K/BOX = MOQ	10K PER 13" REEL (8 mm TAPE), 10K/BOX = MOQ	
		STANDARD	GREEN				
GSOT05-		E		3	-08		GSOT05-E3-08
GSOT05-			G	3	-08		GSOT05-G3-08
GSOT05-	H	E		3	-08		GSOT05-HE3-08
GSOT05-	H		G	3	-08		GSOT05-HG3-08
GSOT05-		E		3		-18	GSOT05-E3-18
GSOT05-			G	3		-18	GSOT05-G3-18
GSOT05-	H	E		3		-18	GSOT05-HE3-18
GSOT05-	H		G	3		-18	GSOT05-HG3-18

PACKAGE DATA							
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
GSOT03	SOT-23	03	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
		03G	Green	8.1 mg			
GSOT04	SOT-23	04	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
		04G	Green	8.1 mg			
GSOT05	SOT-23	05	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
		05G	Green	8.1 mg			
GSOT08	SOT-23	08	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
		08G	Green	8.1 mg			
GSOT12	SOT-23	12	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
		12G	Green	8.1 mg			
GSOT15	SOT-23	15	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
		15G	Green	8.1 mg			
GSOT24	SOT-23	24	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
		24G	Green	8.1 mg			
GSOT36	SOT-23	36	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
		36G	Green	8.1 mg			



ABSOLUTE MAXIMUM RATINGS GSOT03				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	I_{PPM}	30	A
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	P_{PP}	369	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-55 to +150	$^{\circ}\text{C}$

ABSOLUTE MAXIMUM RATINGS GSOT04				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	I_{PPM}	30	A
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	P_{PP}	429	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-55 to +150	$^{\circ}\text{C}$

ABSOLUTE MAXIMUM RATINGS GSOT05				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	I_{PPM}	30	A
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	P_{PP}	480	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-55 to +150	$^{\circ}\text{C}$

ABSOLUTE MAXIMUM RATINGS GSOT08				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	I_{PPM}	18	A
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	P_{PP}	345	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-55 to +150	$^{\circ}\text{C}$



ABSOLUTE MAXIMUM RATINGS GSOT12				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	I_{PPM}	12	A
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	P_{PP}	312	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-55 to +150	$^{\circ}\text{C}$

ABSOLUTE MAXIMUM RATINGS GSOT15				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	I_{PPM}	8	A
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	P_{PP}	230	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-55 to +150	$^{\circ}\text{C}$

ABSOLUTE MAXIMUM RATINGS GSOT24				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	I_{PPM}	5	A
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	P_{PP}	235	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-55 to +150	$^{\circ}\text{C}$

ABSOLUTE MAXIMUM RATINGS GSOT36				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	I_{PPM}	3.5	A
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$; single shot	P_{PP}	248	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-55 to +150	$^{\circ}\text{C}$

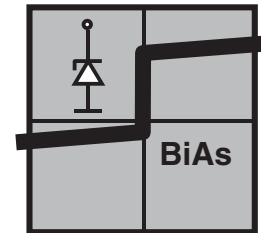
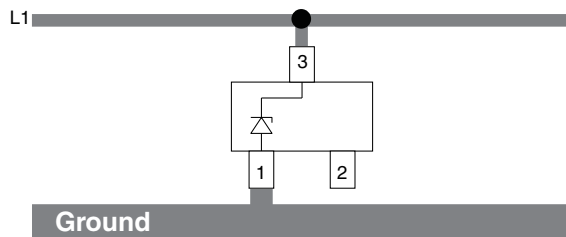
BiAs-MODE (1-line Bidirectional Asymmetrical protection mode)

With the GSOTxx one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 3 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low forward voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxx clamping behavior is Bidirectional and Asymmetrical (BiAs).



20422

ELECTRICAL CHARACTERISTICS GSOT03 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

between pin 3 and pin 1

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	3.3	V
Reverse voltage	at $I_R = 100\text{ }\mu\text{A}$	V_R	3.3	-	-	V
Reverse current	at $V_R = 3.3\text{ V}$	I_R	-	-	100	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	4	4.6	5.5	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	V_C	-	5.7	7.5	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$		-	10	12.3	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	V_F	-	1	1.2	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$		-	4.5	-	V
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	-	420	600	pF
	at $V_R = 1.6\text{ V}$; $f = 1\text{ MHz}$		-	260	-	pF

ELECTRICAL CHARACTERISTICS GSOT04 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

between pin 3 and pin 1

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	4	V
Reverse voltage	at $I_R = 20\text{ }\mu\text{A}$	V_R	4	-	-	V
Reverse current	at $V_R = 4\text{ V}$	I_R	-	-	20	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	5	6.1	7	V



ELECTRICAL CHARACTERISTICS GSOT04 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	V_C	-	7.5	9	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$		-	11.2	14.3	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	V_F	-	1	1.2	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$		-	4.5	-	V
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	-	310	450	pF
	at $V_R = 2\text{ V}$; $f = 1\text{ MHz}$		-	200	-	pF

ELECTRICAL CHARACTERISTICS GSOT05 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	5	V
Reverse voltage	at $I_R = 10\text{ }\mu\text{A}$	V_R	5	-	-	V
Reverse current	at $V_R = 5\text{ V}$	I_R	-	-	10	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	6	6.8	8	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	V_C	-	7	8.7	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$		-	12	16	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	V_F	-	1	1.2	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$		-	4.5	-	V
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	-	260	350	pF
	at $V_R = 2.5\text{ V}$; $f = 1\text{ MHz}$		-	150	-	pF

ELECTRICAL CHARACTERISTICS GSOT08 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	8	V
Reverse voltage	at $I_R = 5\text{ }\mu\text{A}$	V_R	8	-	-	V
Reverse current	at $V_R = 8\text{ V}$	I_R	-	-	5	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	9	10	11	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	V_C	-	10.7	13	V
	at $I_{PP} = I_{PPM} = 18\text{ A}$		-	15.2	19.2	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	V_F	-	1	1.2	V
	at $I_{PP} = I_{PPM} = 18\text{ A}$		-	3	-	V
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	-	160	250	pF
	at $V_R = 4\text{ V}$; $f = 1\text{ MHz}$		-	80	-	pF



ELECTRICAL CHARACTERISTICS GSOT12 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	V_R	12	-	-	V
Reverse current	at $V_R = 12\text{ V}$	I_R	-	-	1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	13.5	15	16.5	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	V_C	-	15.4	18.7	V
	at $I_{PP} = I_{PPM} = 12\text{ A}$		-	21.2	26	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	V_F	-	1	1.2	V
	at $I_{PP} = I_{PPM} = 12\text{ A}$		-	2.2	-	V
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	-	115	150	pF
	at $V_R = 6\text{ V}$; $f = 1\text{ MHz}$		-	50	-	pF

ELECTRICAL CHARACTERISTICS GSOT15 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	15	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	V_R	15	-	-	V
Reverse current	at $V_R = 15\text{ V}$	I_R	-	-	1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	16.5	18	20	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	V_C	-	19.4	23.5	V
	at $I_{PP} = I_{PPM} = 8\text{ A}$		-	24.8	28.8	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	V_F	-	1	1.2	V
	at $I_{PP} = I_{PPM} = 8\text{ A}$		-	1.8	-	V
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	-	90	120	pF
	at $V_R = 7.5\text{ V}$; $f = 1\text{ MHz}$		-	35	-	pF

ELECTRICAL CHARACTERISTICS GSOT24 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	24	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	V_R	24	-	-	V
Reverse current	at $V_R = 24\text{ V}$	I_R	-	-	1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	27	30	33	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	V_C	-	34	41	V
	at $I_{PP} = I_{PPM} = 5\text{ A}$		-	41	47	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	V_F	-	1	1.2	V
	at $I_{PP} = I_{PPM} = 5\text{ A}$		-	1.4	-	V
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	-	65	80	pF
	at $V_R = 12\text{ V}$; $f = 1\text{ MHz}$		-	20	-	pF



ELECTRICAL CHARACTERISTICS GSOT36 ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	36	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	V_R	36	-	-	V
Reverse current	at $V_R = 36\text{ V}$	I_R	-	-	1	μA
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	V_{BR}	39	43	47	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	V_C	-	49	60	V
	at $I_{PP} = I_{PPM} = 3.5\text{ A}$		-	59	71	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	V_F	-	1	1.2	V
	at $I_{PP} = I_{PPM} = 3.5\text{ A}$		-	1.3	-	V
Capacitance	at $V_R = 0\text{ V}$; $f = 1\text{ MHz}$	C_D	-	52	65	pF
	at $V_R = 18\text{ V}$; $f = 1\text{ MHz}$		-	12	-	pF

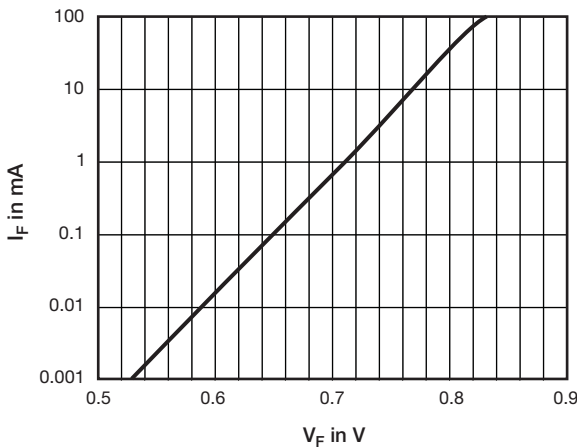


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

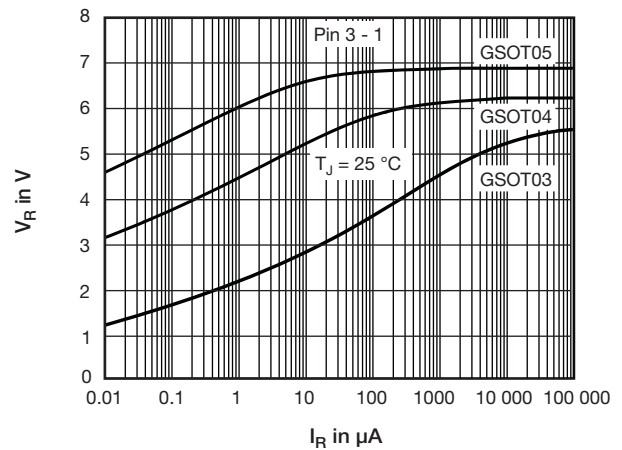


Fig. 3 - Typical Reverse Voltage V_R vs. Reverse Current I_R

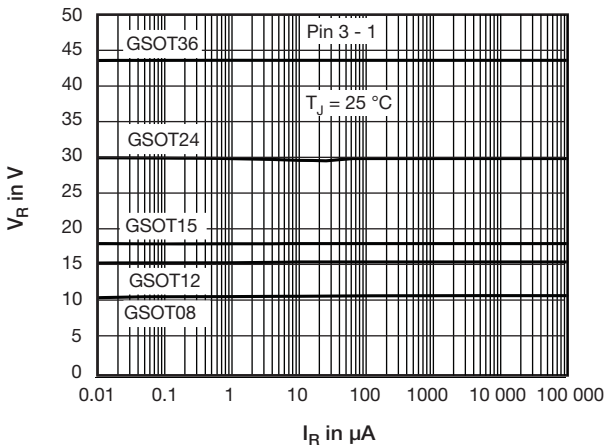
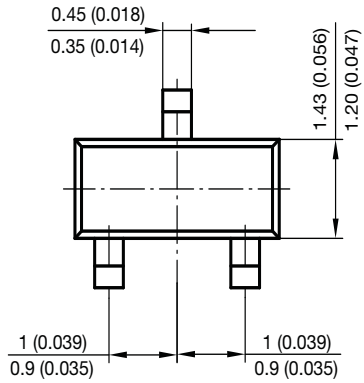
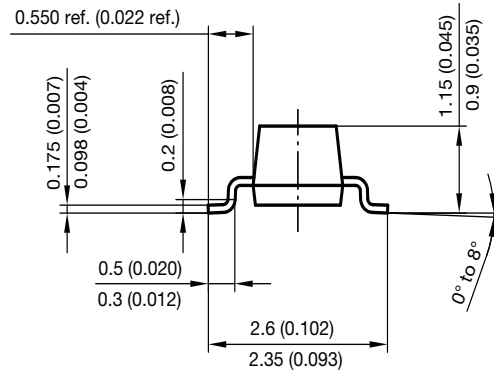
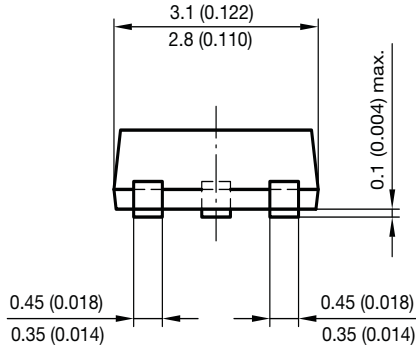


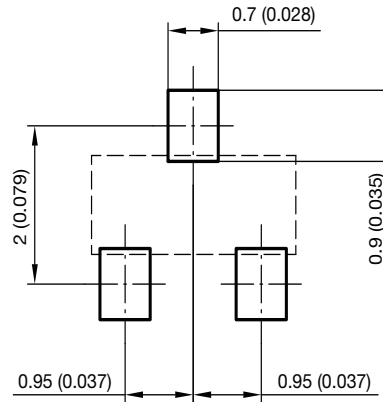
Fig. 2 - Typical Reverse Voltage V_R vs. Reverse Current I_R



PACKAGE DIMENSIONS in millimeters (inches): **SOT-23**

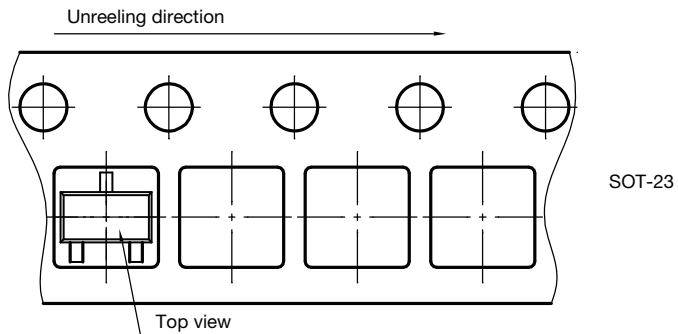


Foot print recommendation:



Document no.: 6.541-5014.01-4
 Rev. 8 - Date: 23.Sept.2009
 17418

Orientation in carrier tape
 SOT-23
 S8-V-3929.01-006 (4)
 04.02.2010
 22607





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